



European Network on New Sensing Technologies for Air Pollution Control and Environmental Sustainability - *EuNetAir*

COST Action TD1105

**WGs and MC Meeting at Cambridge, 18-20 December 2013**

**On the direct coupling of nanostructured metal oxides and resistive silicon micro hotplate transducers**



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# Integration of low-dimensional gas sensitive metal oxides onto transducers

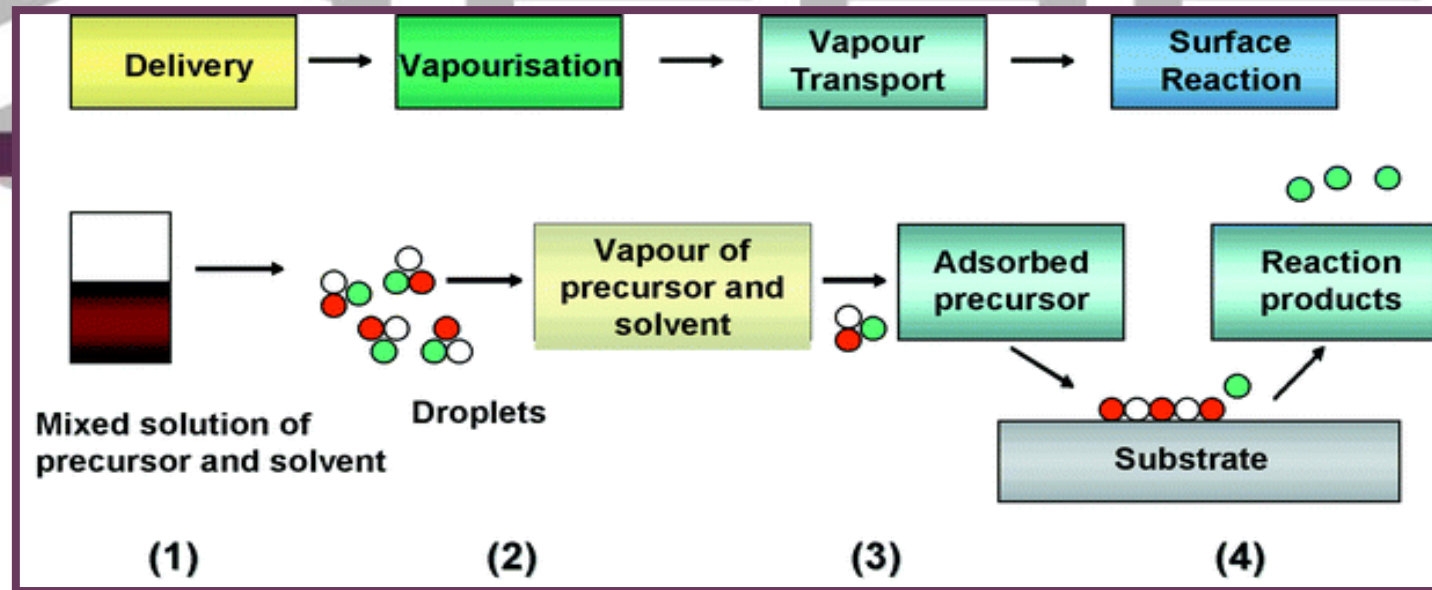
## Promises

- LDMOX offer very high specific surface area
- Precise surface composition control (case of single crystalline NWs)
- Possibility of NW growth and surface functionalisation
- Integration of MOX nanotubes using smart anodization compatible with Microsystems technology

## Needs

- Avoid the need of surface pre-treatment for substrates
- Use moderate growth temperatures (for being compatible with different substrates)
- Use scalable methods for mass-production of nanomaterials

# Aerosol-Assisted CVD (VS)



- (1) The precursor(s) is (are) dissolved in an organic solvent. (Single source) Enables synthesis of multicomponent materials with controlled stoichiometry.
- (2) The mixture is converted into droplets by an ultrasonic modulator. (Simple)
- (3) The aerosol of precursor and solvent are transported by a carrier gas into a hot zone where it evaporates.
- (4) The vapor of the precursor is then transported to the substrate where it adsorbs and reacts to form a film.
- (5) Allows rapid formation of the deposited phases at relatively low temperatures due to the small diffusion distances between reactant and intermediates.
- (6) Low cost process since the AA-CVD can be performed in an open atmosphere.

# Aerosol-Assisted CVD (VS)

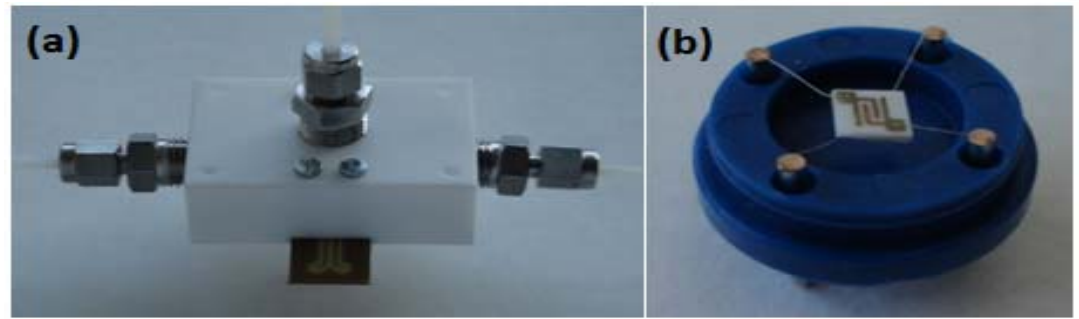


Hot wall AACVD reactor

**Deposition time: 45-60 min**

**Precursor : 150 mg**

**T °C used : up to 500 °C**



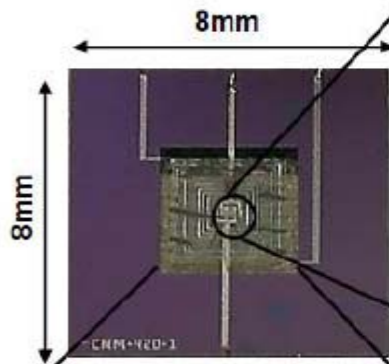
(a) AACVD cold wall reactor, (b) Alumina gas sensor

**Deposition time: 15-20 min**

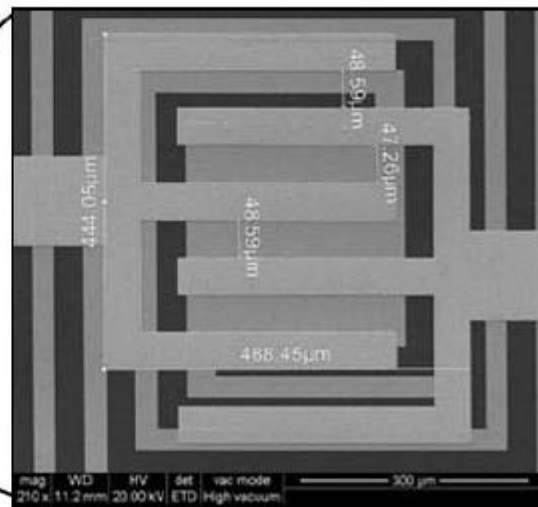
**Precursor : 50 mg**

**T °C used : up to 600 °C**

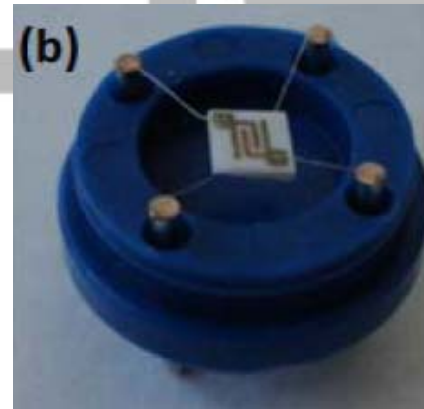




(a)

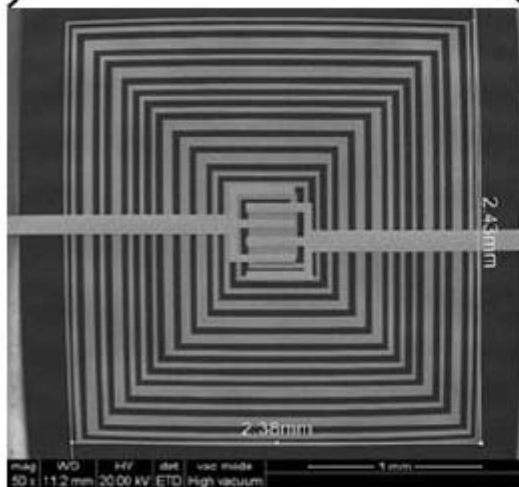


(c)

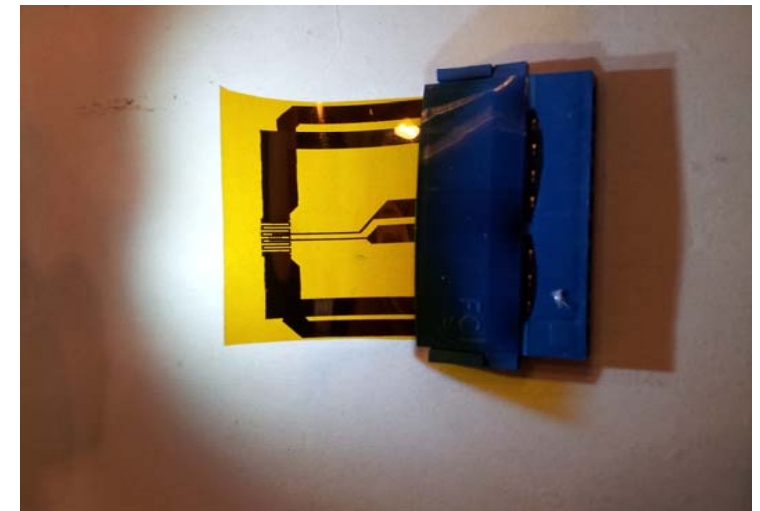
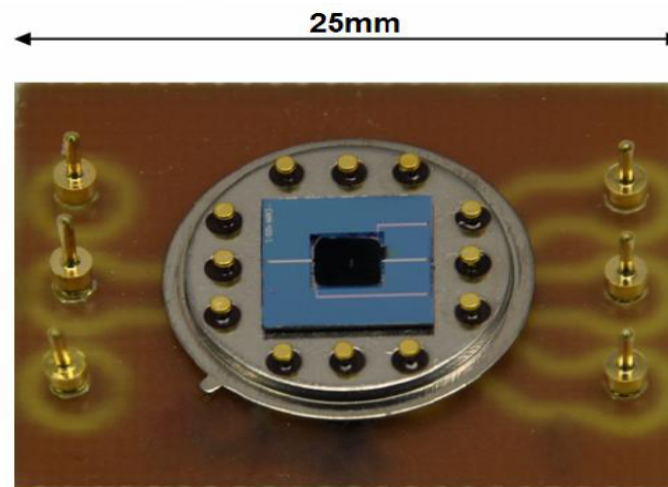


(b)

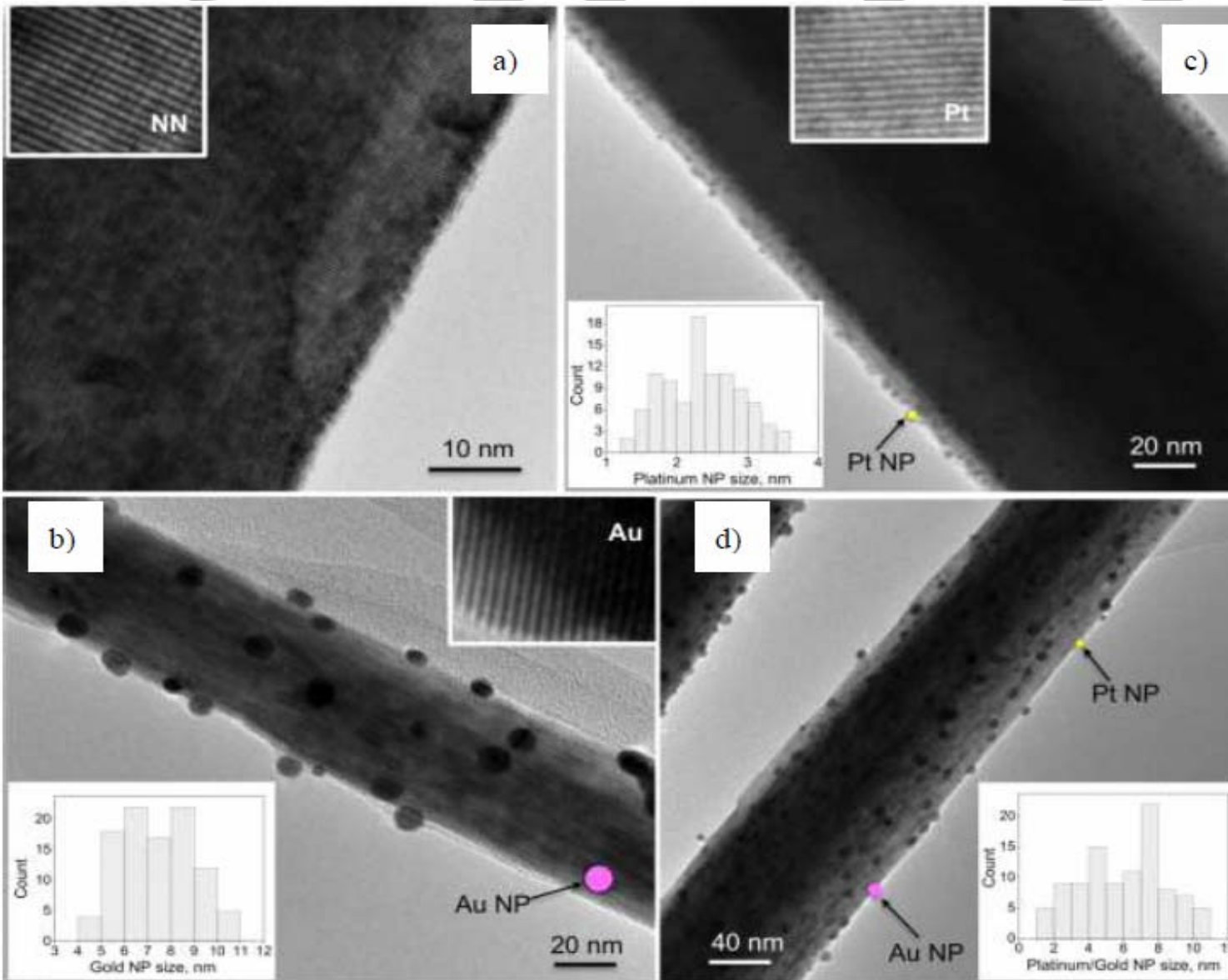
Direct growth of NWs on ceramic, micromachined silicon and flexible substrates



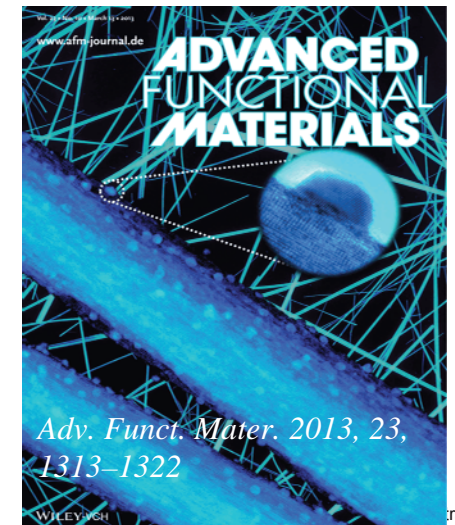
(b)



# Characterization (TEM and HRTEM)

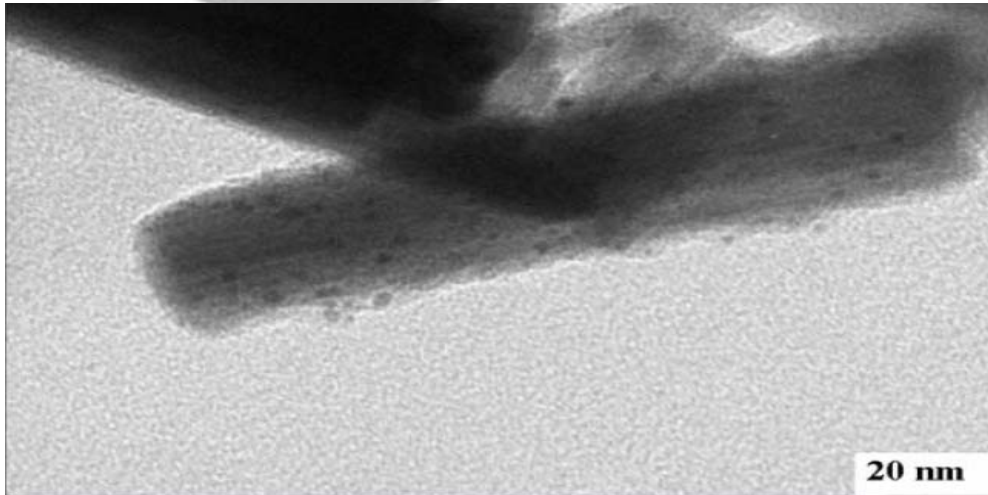


Intrinsic (a) and functionalized samples with gold (b), platinum (c), and gold/platinum (d)  $W(OPh)_6$  (acetone);  $HAuCl_4 \cdot 3H_2O$ ,  $H_2PtCl_6 \cdot xH_2O$ , (methanol) At 350-450°C



# Characterization (TEM)

Precursors:  $W(OPh)_6$   
(acetone); Copper (II)  
acetylacetonate  
 $[Cu(C_5H_7O_2)_2]$  (methanol)  
Growth: At  $350^\circ C$   
Particle size: 4-8 nm

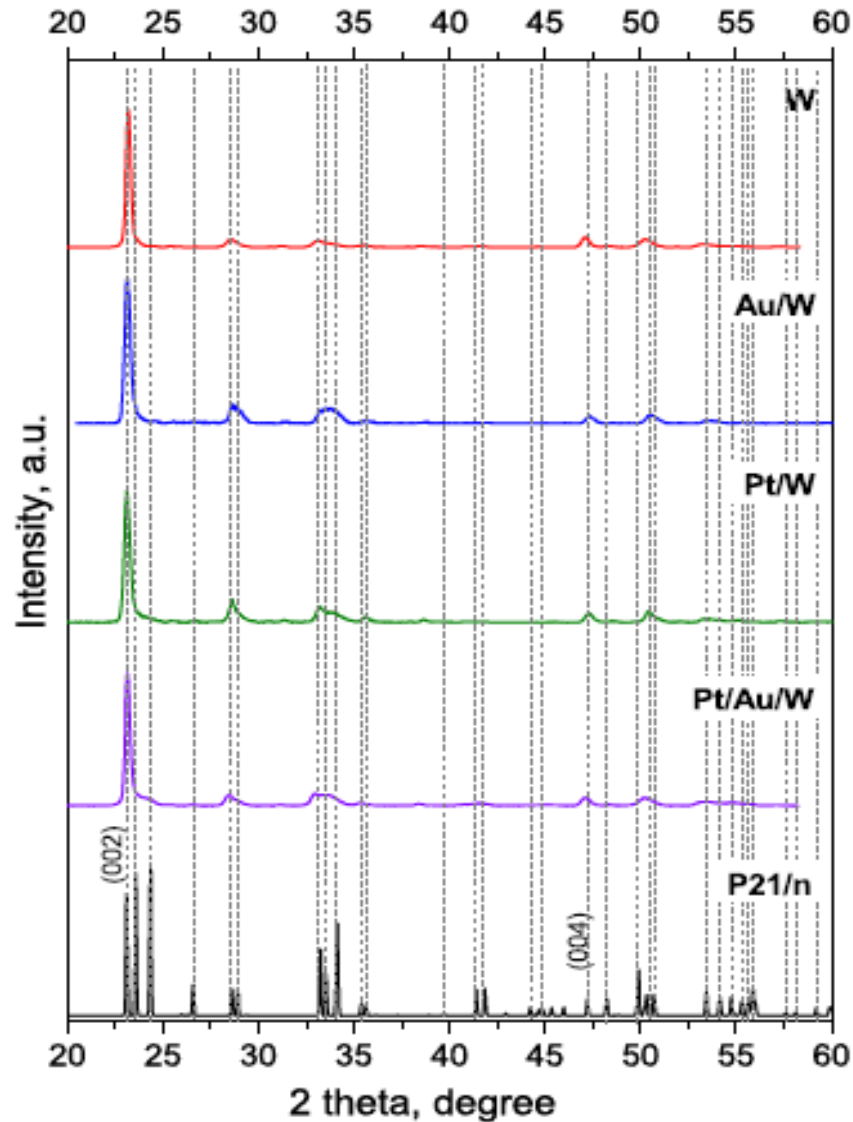


*Thin Solid Films, 548 (2013) 703-709*

All  $WO_3$  NWs with lengths of  $\approx 7 \mu m$  and diameters ranging between 60 and 120 nm, corresponding to aspect ratios of  $\approx 60-115$ .

Metal NPs remain stable even when NW mats are annealed at  $500^\circ C$  in air for 2 hours.

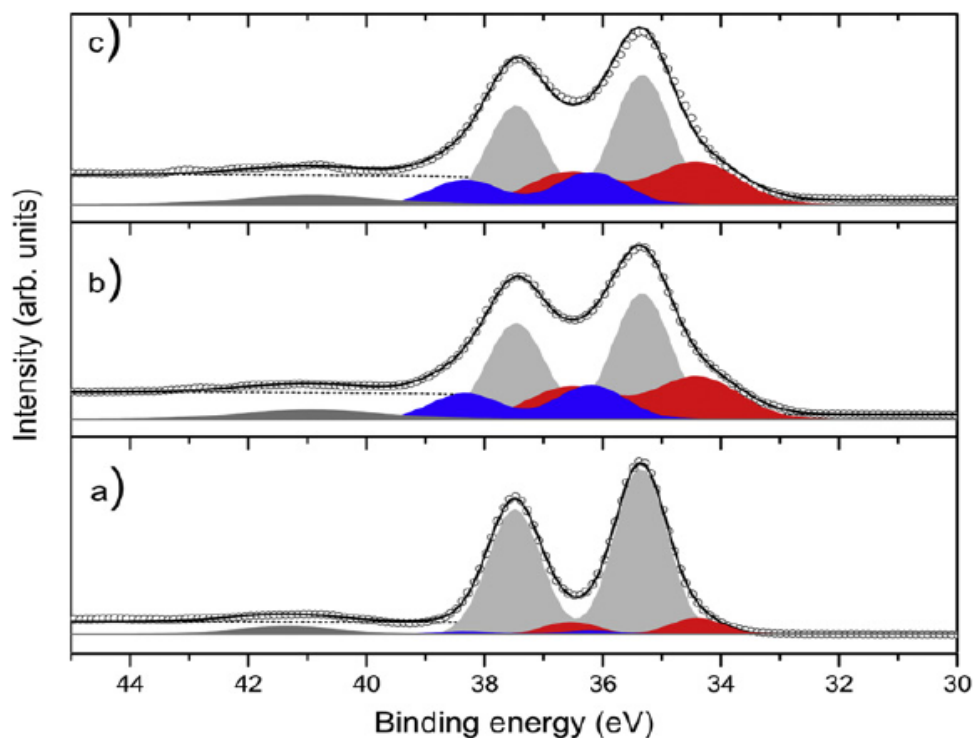
# Characterization (XRD)



XRD patterns of the (from top to bottom) non-functionalised, functionalised films with gold, Platinum, gold/platinum and typical diffractions of monoclinic phase (ICCD card no. 72-0677).

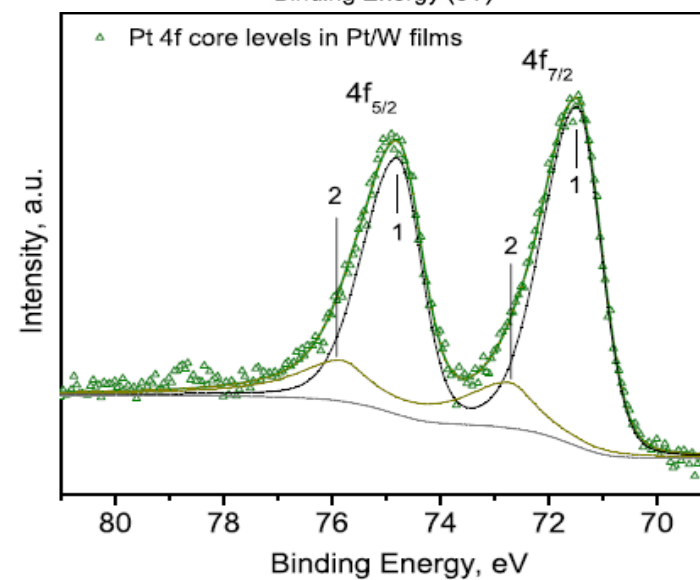
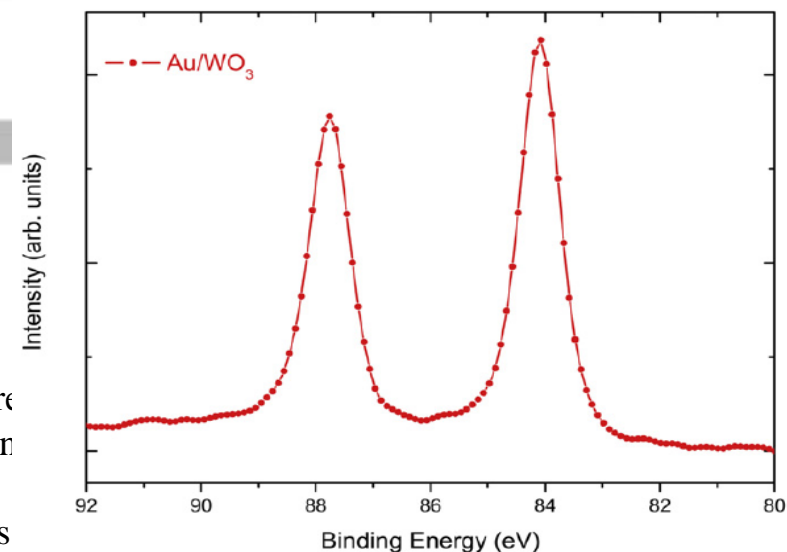


# Characterization (XPS)

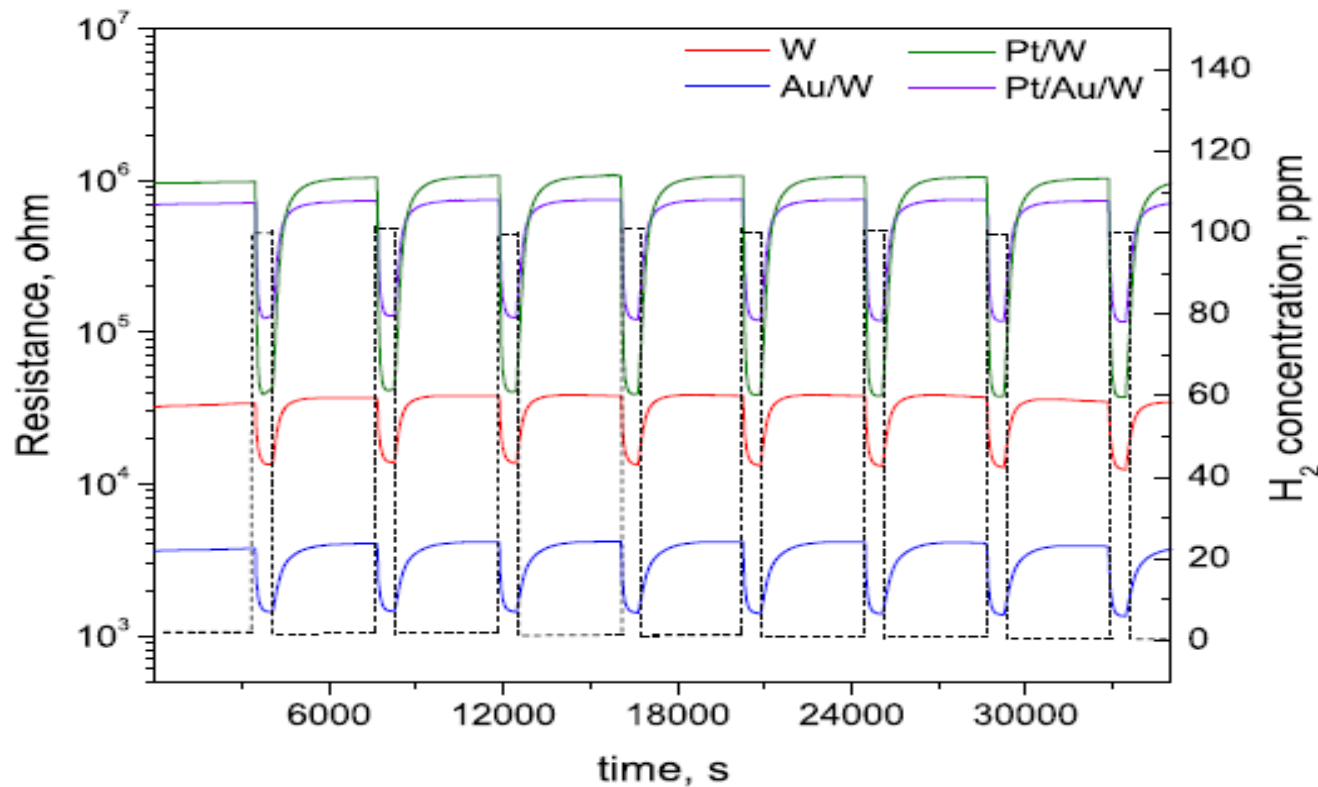
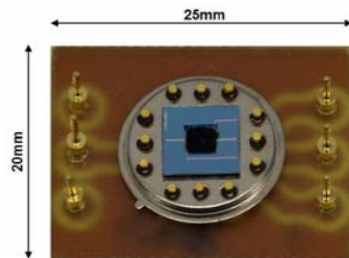


XPS core levels for pristine  $\text{WO}_3$  powder (a),  $\text{WO}_3$  NWs (b) and Au on  $\text{WO}_3$  NWs (c). Light gray: W4f level for stoichiometric  $\text{WO}_3$ . Red: W4f level for sub-stoichiometric  $\text{WO}_{3-x}$ . Blue: W 4f level of W atoms near surface defects.

Au and Pt 4f core level recorded on Au/ $\text{WO}_3$  and Pt/ $\text{WO}_3$  samples

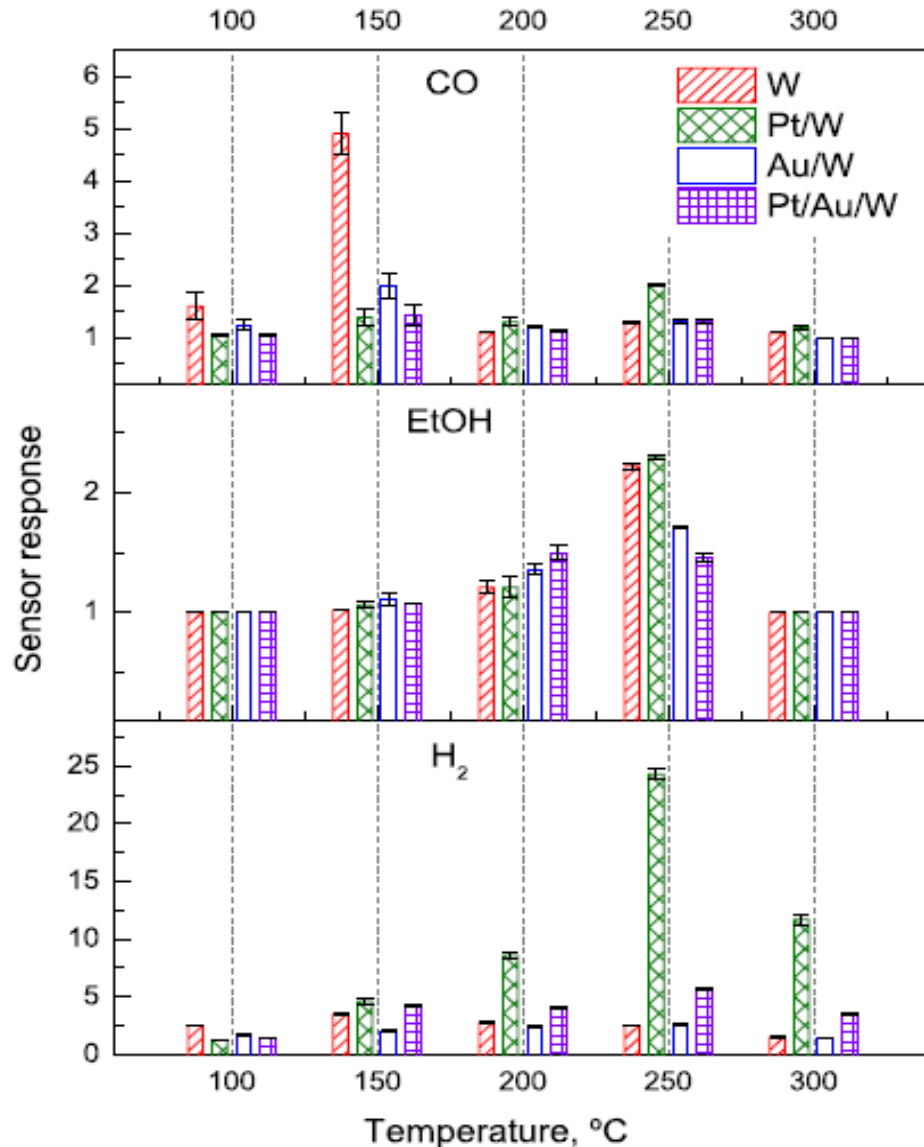


# Gas sensing properties of tungsten oxide NWs (Silicon micromachined substrates)



Film resistance changes towards hydrogen 100 ppm at 250 °C.

# Gas sensing properties of tungsten oxide NWs (Silicon micromachined substrates)

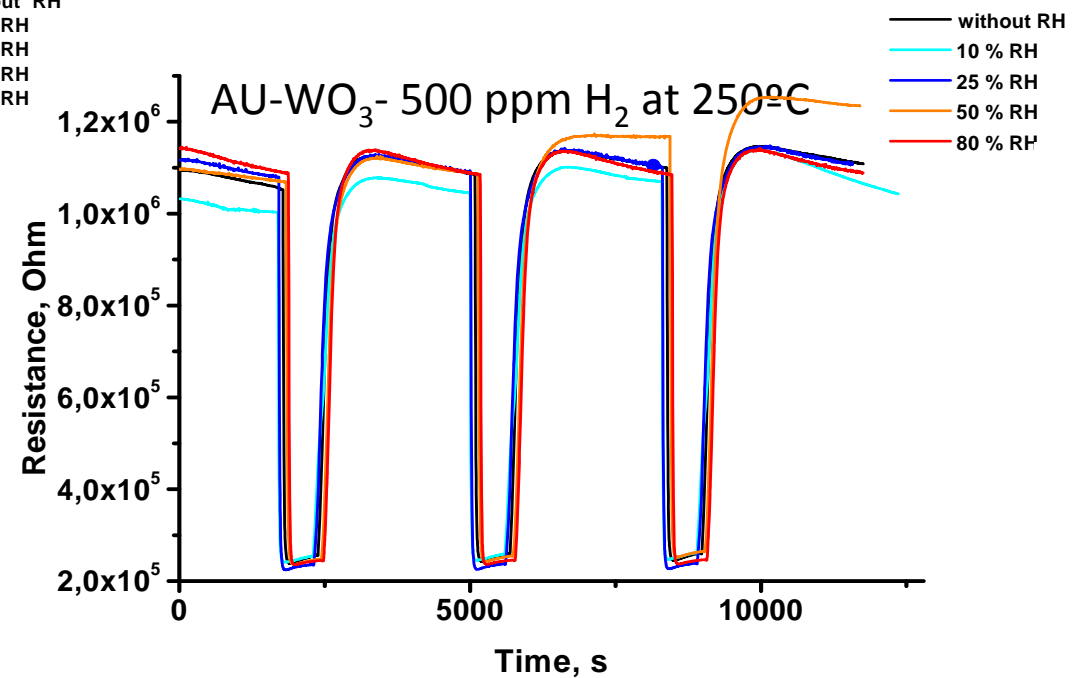
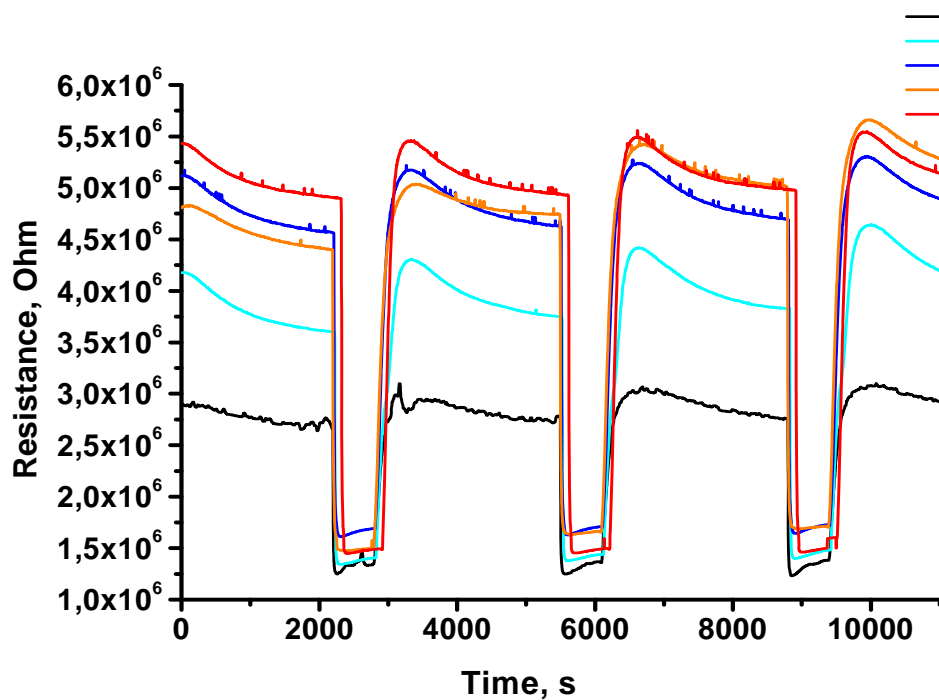


Sensor responses and error bars to 100 ppm of CO, 2 ppm of EtOH, and 100 ppm of H<sub>2</sub>, as a function of the operating temperature.

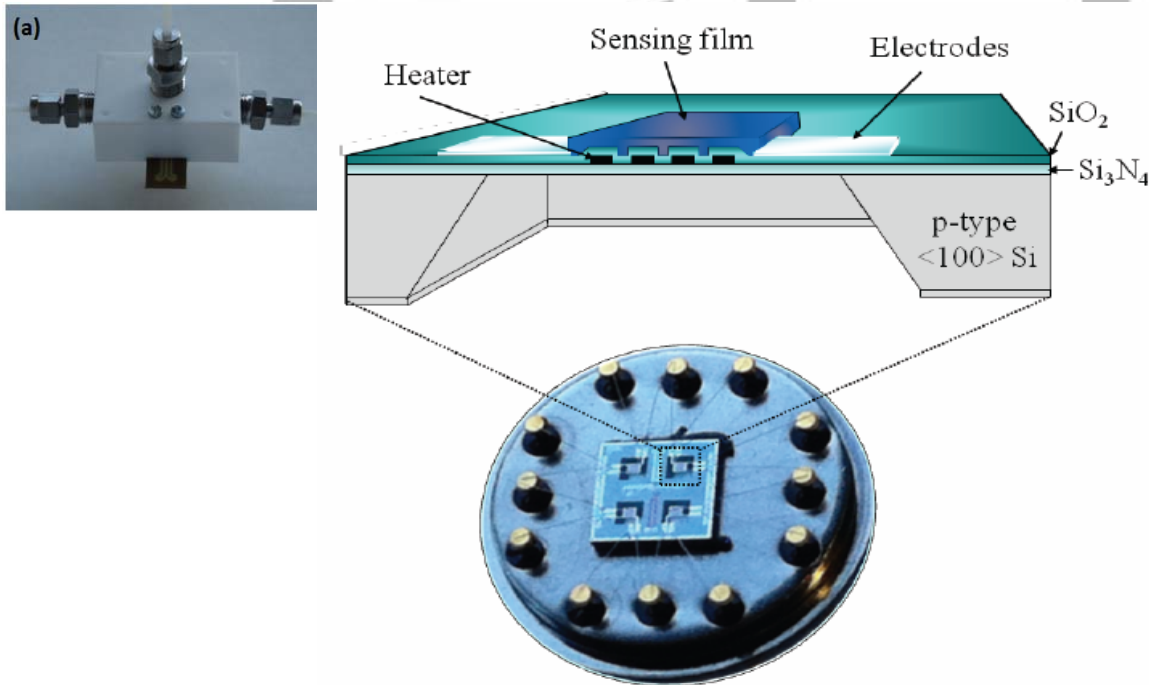
# Gas sensing properties of tungsten oxide NWs (Silicon micromachined substrates)

## Humidity effect

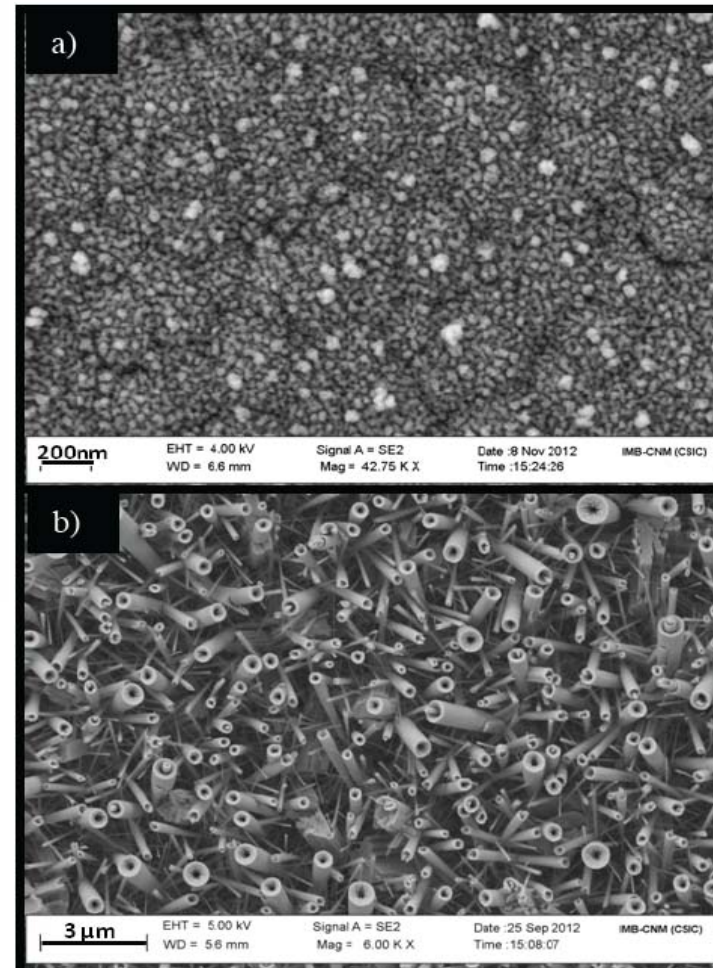
WO<sub>3</sub> - 500 ppm H<sub>2</sub> at 250°C



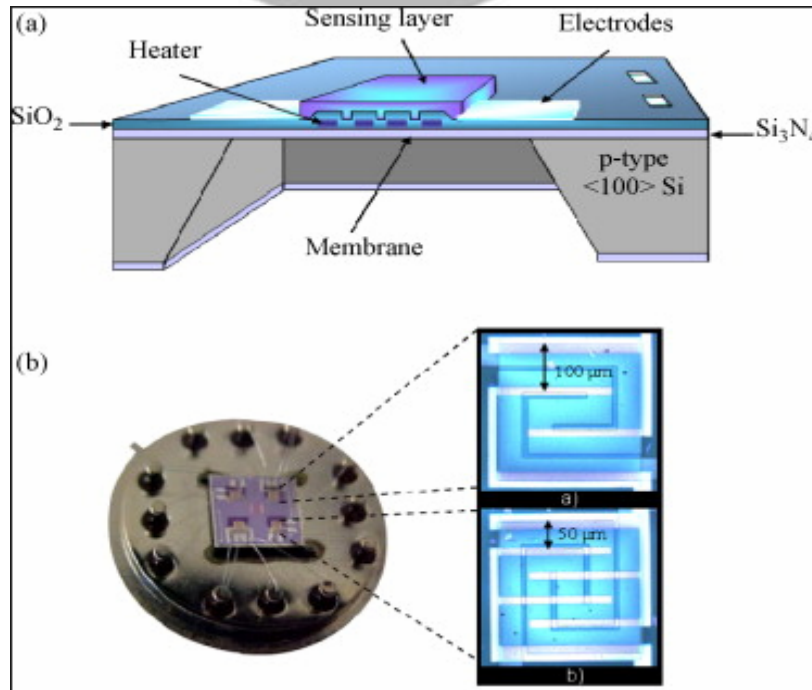
# Growth of $MO_x$ NWs using the heater embedded in micro-hotplates



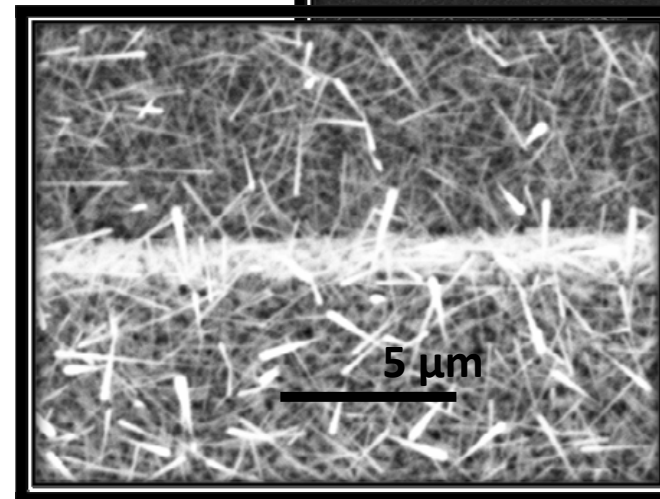
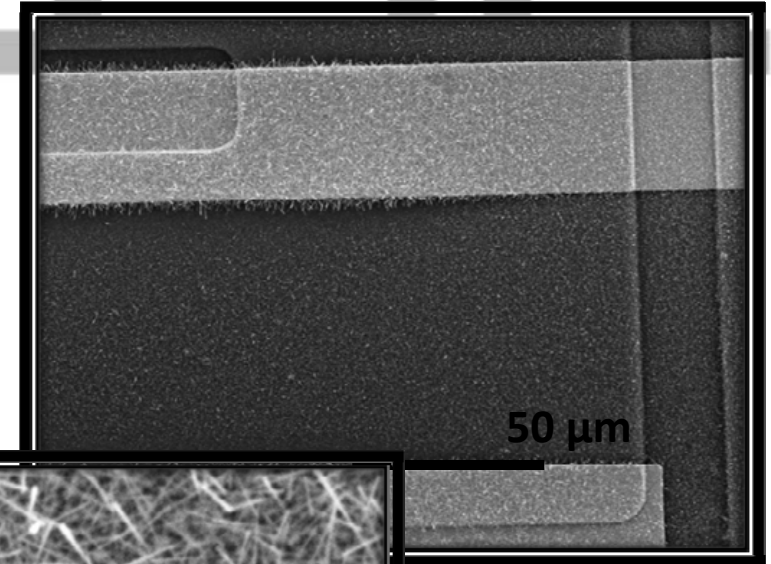
Direct growth of nanomaterials onto micro-hotplate transducers using the integrated heating element to reach and keep reaction temperature during growth.



# Growth of $MO_x$ NWs using the heater embedded in micro-hotplates

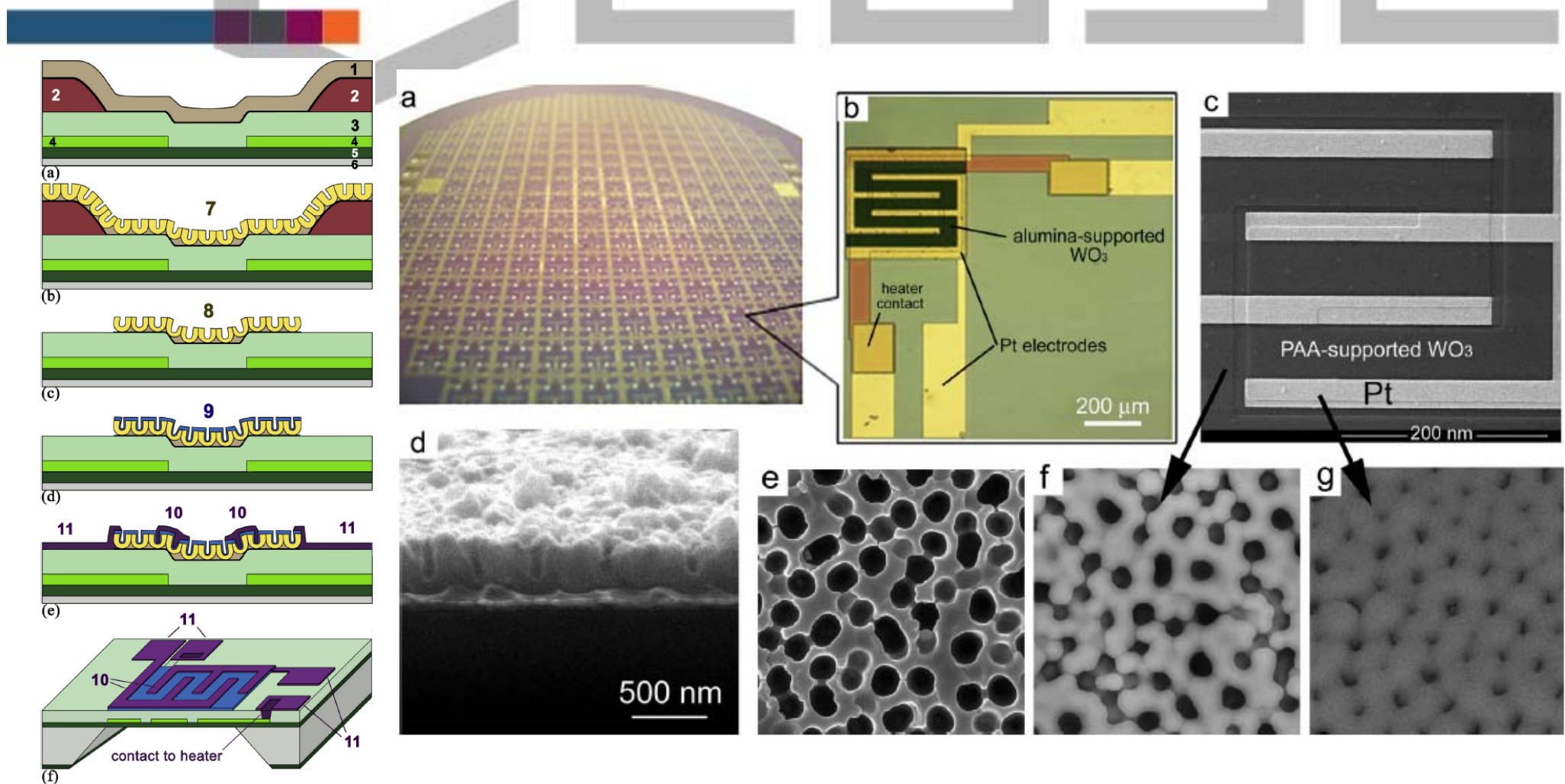


*Schematic view of the micromachined membrane section and view of the 4-microsensors mounted on standard TO-8*

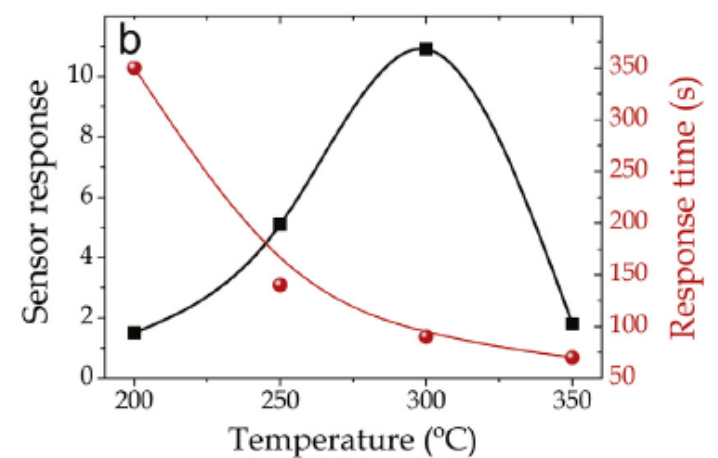
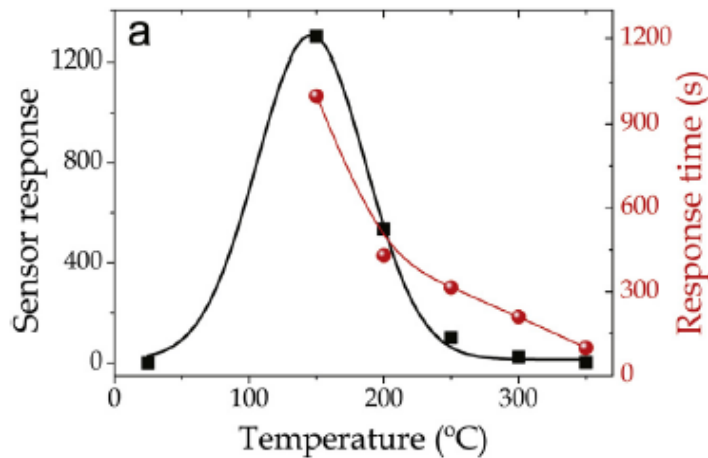
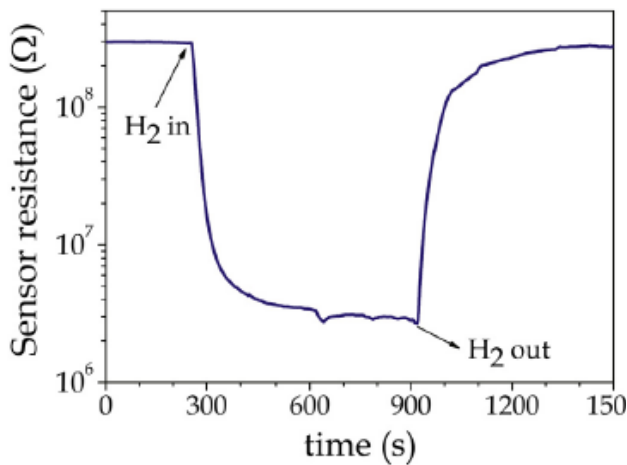
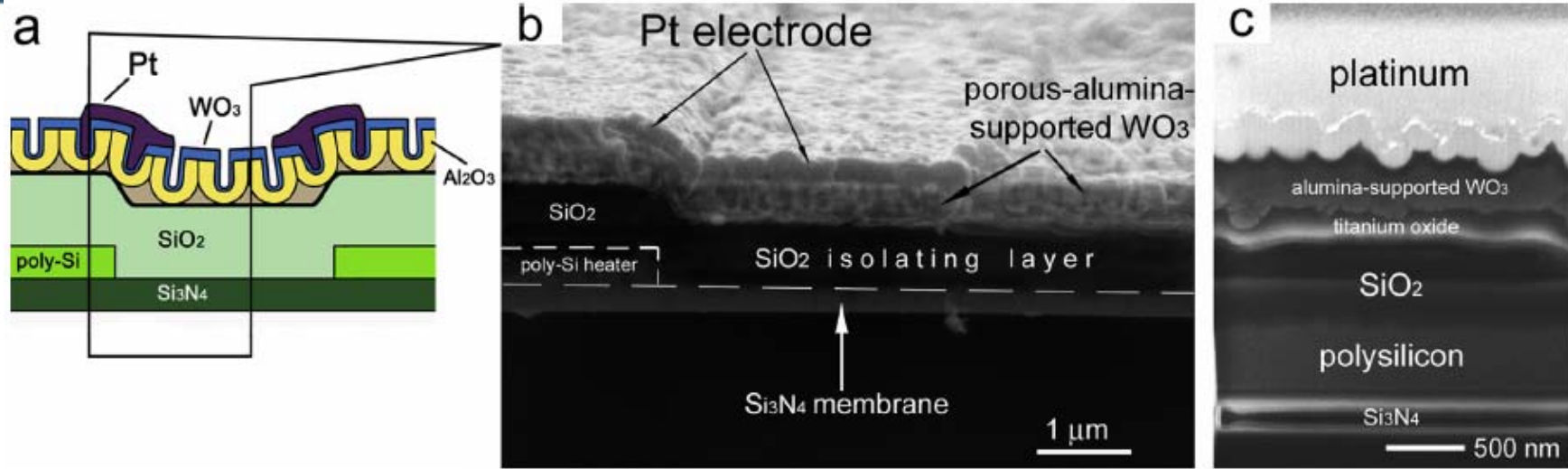


$WO_3$  nanowires deposited on silicon substrate at 600  $^{\circ}C$  using cold wall reactor

# MOX nanotubes by smart anodization



# MOX nanotubes by smart anodization





# Conclusions

- AA-CVD is a flexible, simple and scalable process for the bottom up integration of NWs in MEMS. One-step growth and decoration of NWs
- Metal decorated tungsten oxide NW sensors show a stable response and baseline (drift below 8% in 12 months)
- Smart anodization is a MEMS compatible strategy for integrating MOX nanostructures onto microhotplates. Sensitivity is highly increased